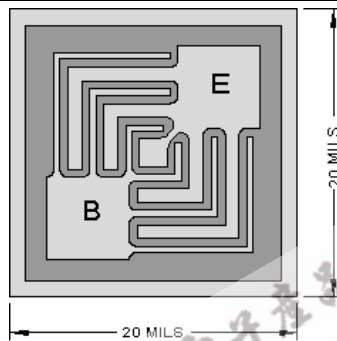


Chip Type 2C2222A
Geometry 0400
Polarity NPN

Generic Packaged Parts:

**2N2219, 2N2219A, 2N2222,
 2N2222A**



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Chip type **2C2222A** by Semicoa Semiconductors provides performance similar to these devices.

Part Numbers:

[2N2222A](#), [2N2222](#), [2N2219](#), [2N2219A](#), [2N2219AL](#),
[2N2222AUB](#), [SD2222A](#), [SD2222AF](#), [SQ2222A](#),
[SQ2222AF](#), [2N5582](#), [2N6989](#), [2N6990](#)

Product Summary:

APPLICATIONS: Designed for general purpose switching and amplifier applications.

Features: Medium power ratings

Mechanical Specifications

Metallization	Top	Al - 24 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	4.0 mils x 4.0 mils
	Base	4.0 mils x 4.0 mils
Die Thickness	8 mils nominal	
Chip Area	20 mils x 20 mils	
Top Surface	Silox Passivated	

Electrical Characteristics

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
BV_{CEO}	$I_C = 10 \text{ mA}$, $I_B = 0$	40	---	V dc
BV_{CBO}	$I_C = 10 \text{ }\mu\text{A}$, $I_E = 0$	75	---	V dc
BV_{EBO}	$I_E = 10 \text{ }\mu\text{A}$, $I_C = 0$	6.0	---	V dc
I_{CBO}	$V_{CB} = 50 \text{ V}$, $I_E = 0$	---	10	nA dc
h_{FE}	$I_C = 150 \text{ mA dc}$, $V_{CE} = 10 \text{ V}$	100	300	---

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 μs , duty cycle less than 2%.